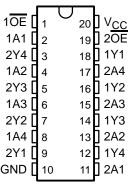
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- **EPIC™** (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V<sub>OLP</sub> (Output Ground Bounce)
  < 0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot)
  2 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V<sub>CC</sub>)
- Package Options Include Shrink Small-Outline (DB), Plastic Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages

# DB, DW, OR PW PACKAGE (TOP VIEW)



#### description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V<sub>CC</sub> operation.

The SN74LVC244A is organized as two 4-bit line drivers with separate output-enable ( $\overline{OE}$ ) inputs. When  $\overline{OE}$  is low, the device passes data from the A inputs to the Y outputs. When  $\overline{OE}$  is high, the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC244A is characterized for operation from -40°C to 85°C.

# FUNCTION TABLE (each buffer)

INPUTS		OUTPUT
OE	Α	Y
L	Н	Н
L	L	L
Н	Χ	Z

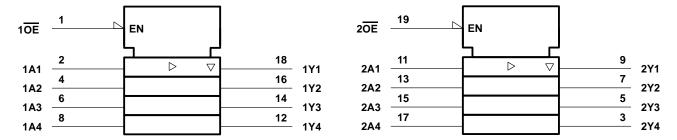


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#### logic symbol†



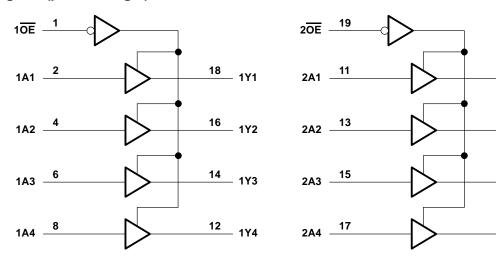
9 2Y1

7 2Y2

5 2Y3

3 2Y4

### logic diagram (positive logic)





<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Supply voltage range, V <sub>CC</sub>		–0.5 V to 6.5 V
	Input voltage range, V <sub>I</sub> (see Note 1)		–0.5 V to 6.5 V
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	Voltage range applied to any output in the high-impedance or	power-off state, VO	
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	(see Note 1)		–0.5 V to 6.5 V
$\begin{array}{llllllllllllllllllllllllllllllllllll$	Voltage range applied to any output in the high or low state, V	O	
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	(see Notes 1 and 2)		$1.0-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0 )		
Continuous current through $V_{CC}$ or GND	Output clamp current, $I_{OK}$ ( $V_O < 0$ or $V_O > V_{CC}$ )		±50 mA
Continuous current through $V_{CC}$ or GND	Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$ (see Note 2).		±50 mA
DW package			
PW package 0.7 W	Maximum power dissipation at $T_A = 55^{\circ}$ C (in still air) (see Note	e 3): DB package	0.6 W
PW package 0.7 W		DW package	1.6 W
	Storage temperature range, T <sub>stg</sub>		

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 2. The value of  $V_{\hbox{\scriptsize CC}}$  is provided in the recommended operating conditions table.
  - 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*.

#### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V	Operating	Operating	2	3.6	V
Vcc	Supply voltage Data retention only		1.5		V
V <sub>IH</sub>	High-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
V <sub>IL</sub>	Low-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	V
٧ <sub>I</sub>	Input voltage		0	5.5	V
Va	Output voltage	High or low state	0	VCC	V
۷o		3 state	0	5.5	V
lau	High-level output current $ \frac{V_{CC} = 2.7 \text{ V}}{V_{CC} = 3 \text{ V}} $		-12	mA	
ЮН		V <sub>CC</sub> = 3 V		-24	l IIIA
lai	V <sub>CC</sub> = 2.7 V		12	mA	
IOL	Low-level output current	V <sub>CC</sub> = 3 V		24	IIIA
Δt/Δν	Input transition rise or fall rate		0	10	ns/V
TA	Operating free-air temperature		-40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.



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#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CO	ONDITIONS	VCC	MIN	TYP <sup>†</sup>	MAX	UNIT
	$I_{OH} = -100 \mu\text{A}$		2.7 V to 3.6 V	V <sub>CC</sub> -0.2			
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	la., 40 mA		2.7 V	2.2			٧
VOH	IOH = -12 IIIA	OH = -12  mA		2.4			
	I <sub>OH</sub> = -24 mA		3 V	2.2			
	I <sub>OL</sub> = 100 μA	I <sub>OL</sub> = 100 μA				0.2	
V <sub>OL</sub>	I <sub>OL</sub> = 12 mA		2.7 V			0.4	V
	I <sub>OL</sub> = 24 mA		3 V			0.55	
lį	V <sub>I</sub> = 0 to 5.5 V		3.6 V			±5	μΑ
l <sub>off</sub>	$V_I$ or $V_O = 5.5 V$		0			±50	μΑ
loz	V <sub>O</sub> = 0 to 5.5 V		2.7 V to 3.6 V			±10	μΑ
loo	$V_I = V_{CC}$ or GND	1- 0	3.6 V		10		
lcc	$3.6 \text{ V} \le \text{V}_{\text{I}} \le 5.5 \text{ V}^{\ddagger}$	IO = 0	3.6 V			10	μA
∆lCC	One input at V <sub>CC</sub> – 0.6 V,	Other inputs at V <sub>CC</sub> or GND	2.7 V to 3.6 V			500	μΑ
C <sub>i</sub>	$V_I = V_{CC}$ or GND		3.3 V		3.1		pF
Co	$V_O = V_{CC}$ or GND		3.3 V		5		pF

 $<sup>\</sup>dagger$  All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.  $\ddagger$  This applies in the disabled state only.

# switching characteristics over recommended operating free-air temperature range, $C_L$ = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 2.7 V		UNIT
	(INFO1)	(001701)	MIN	MAX	MIN	MAX	
<sup>t</sup> pd	А	Υ	1.5	6.5		7.5	ns
<sup>t</sup> en	ŌE	Υ	1.5	8		9	ns
<sup>t</sup> dis	ŌE	Υ	1.5	7		8	ns
t <sub>sk(o)</sub> §				1			ns

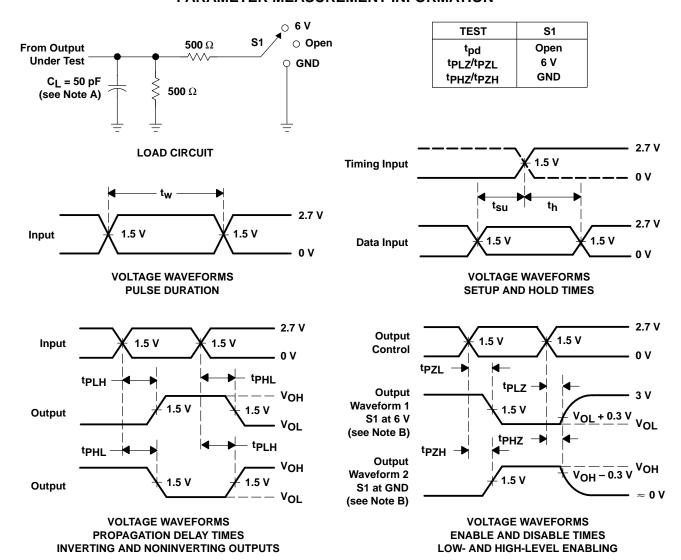
<sup>§</sup> Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

## operating characteristics, $V_{CC} = 3.3 \text{ V}$ , $T_A = 25^{\circ}\text{C}$

PARAMETER			TEST COI	TYP	UNIT	
<b>C</b> .	Dougs dissination consistence nor huffer/driver	Outputs enabled	C: 50 pF	f 10 MH=	30	~ ا
Cpd	Power dissipation capacitance per buffer/driver	Outputs disabled	$C_L = 50 \text{ pF},$	f = 10 MHz	2	pF



#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_0 = 50 \Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpzL and tpzH are the same as ten.
- F. tpLz and tpHz are the same as t<sub>dis</sub>.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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